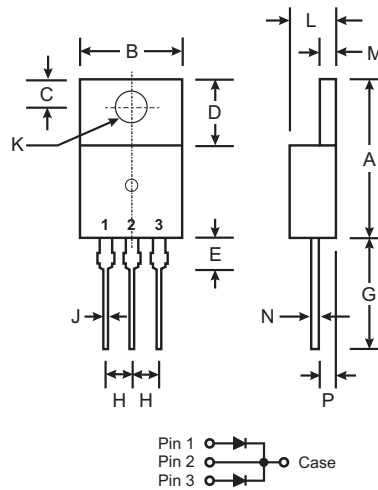


Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- **Lead Free Finish, RoHS Compliant (Note 3)**

Mechanical Data

- Case: TO-220AB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Polarity: As Marked on Body
- Terminals: Finish – Bright Tin. Solderable per MIL-STD-202, Method 208
- Marking: Type Number
- Weight: 2.24 grams (approx.)



TO-220AB		
Dim	Min	Max
A	14.48	15.75
B	10.00	10.40
C	2.54	3.43
D	5.90	6.40
E	2.80	3.93
G	12.70	14.27
H	2.40	2.70
J	0.69	0.93
K	3.54	3.78
L	4.07	4.82
M	1.15	1.39
N	0.30	0.50
P	2.04	2.79
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1030CT	MBR 1035CT	MBR 1040CT	MBR 1045CT	MBR 1050CT	MBR 1060CT	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	30	35	40	45	50	60	V
Working Peak Reverse Voltage	V _{RWM}							
DC Blocking Voltage	V _R							
RMS Reverse Voltage	V _{R(RMS)}	21	24.5	28	31.5	35	42	V
Average Rectified Output Current (Note 1)	I _O	10						A
		@ T _C = 105°C						
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	125						A
Repetitive Peak Reverse Surge Current	I _{RSM}	1.0						A
		@ t ≤ 2.0μs						
Forward Voltage Drop	V _{FM}		0.57			0.70		V
		@ I _F = 5.0A, T _C = 125°C				@ I _F = 5.0A, T _C = 25°C		
		@ I _F = 5.0A, T _C = 25°C		0.70		0.80		
		@ I _F = 10A, T _C = 25°C		0.84		0.95		
Peak Reverse Current at Rated DC Blocking Voltage	I _{RM}				0.1			mA
					15			
Typical Junction Capacitance (Note 2)	C _j				150			pF
Typical Thermal Resistance Junction to Case (Note 1)	R _{θJC}				30			K/W
Voltage Rate of Change (Rated V _R)	dV/dt				1000			V/μs
Operating and Storage Temperature Range	T _J , T _{STG}				-65 to +150			°C

- Notes:
1. Thermal resistance junction to case mounted on heatsink.
 2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
 3. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see *EU Directive Annex Notes 5 and 7*.

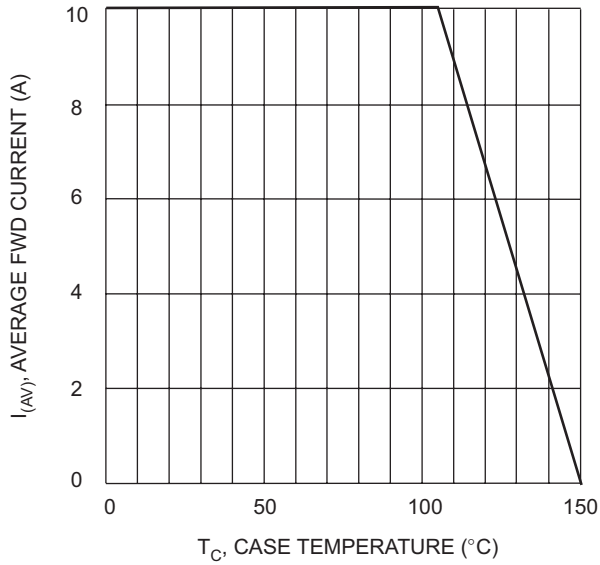


Fig. 1 Forward Current Derating Curve

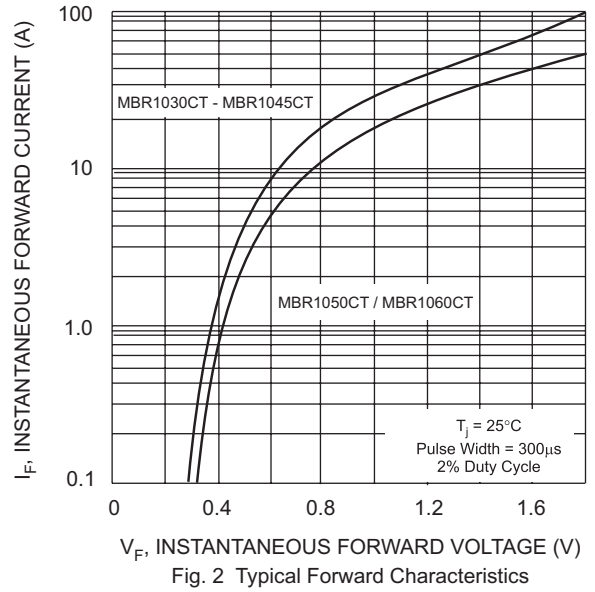


Fig. 2 Typical Forward Characteristics

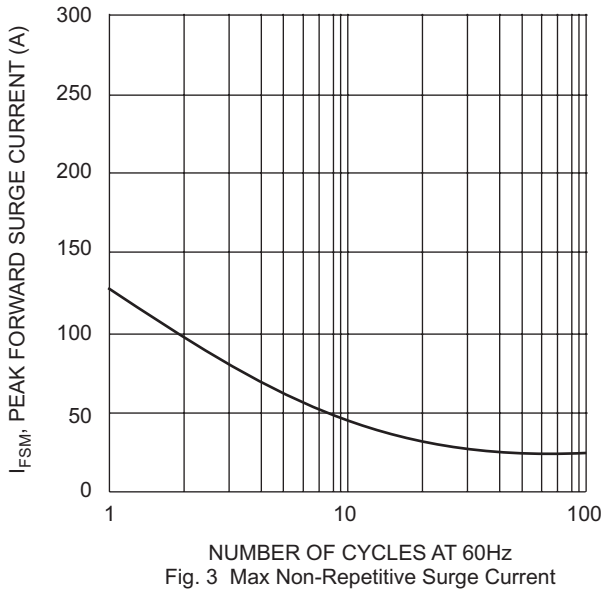


Fig. 3 Max Non-Repetitive Surge Current

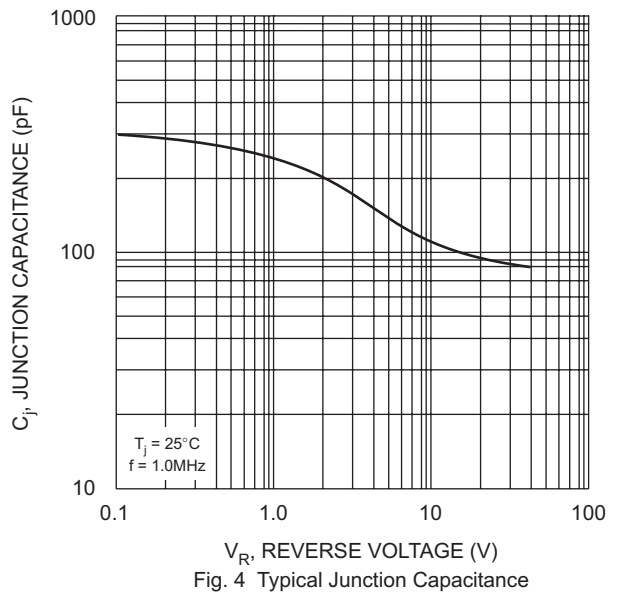


Fig. 4 Typical Junction Capacitance

Ordering Information (Note 4)

Device	Packaging	Shipping
MBR10xxCT*	TO-220AB	50/Tube

* xx = Device type, e.g. MBR1045CT

Notes: 4. For packaging details, visit our website at <http://www.diodes.com/datasheets/ap02008.pdf>.